



YJL3134KAT

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	20 V
I_D	0.5 A
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	300 mohm
$R_{DS(ON)}$ (at $V_{GS}=2.5V$)	400 mohm
$R_{DS(ON)}$ (at $V_{GS}=1.8V$)	700 mohm
ESD Protected Up to 2.0KV (HBM)	

General Description

Trench Power LV MOSFET technology
High Power and current handing capability

Applications

PWM application
Load switch

Absolute Maximum Ratings ($T_A=25$ unless otherwise noted)

Parameter	Symbol	Limit
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Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
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Typical Electr13(0G1320)17()-4(E)-0)17()-4nd-11(t)-0(pi)1h)240)7(rmt)-0)-4(E)-0)17C-11haer13(0G(t)7(r320(c)

YJ



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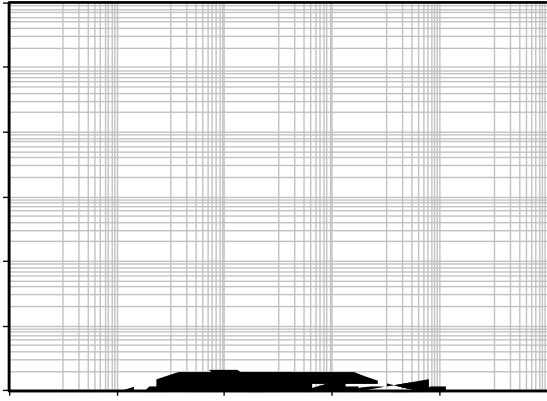


Figure 13. Maximum Transient Thermal Impedance

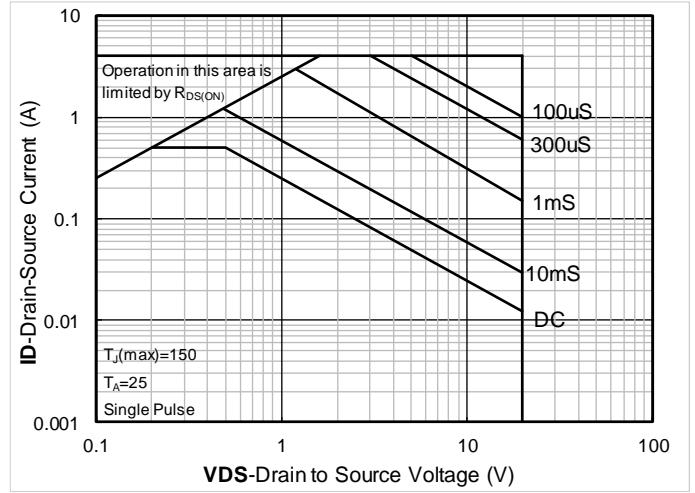


Figure14. Safe Operation Area

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